Vishay Semiconductors

ROHS COMPLIANT

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Hyperfast Rectifier, 15 A FRED Pt®



TO-252AA (D-PAK)

PRODUCT SUMMARY								
Package	TO-252AA (D-PAK)							
I _{F(AV)}	15 A							
V _R	600 V							
V _F at I _F	1.5 V							
t _{rr} (typ.)	18 ns							
T _J max.	175 °C							
Diode variation	Single die							

FEATURES

- Hyperfast recovery time, extremely low Q_{rr}
- 175 °C maximum operating junction temperature
- For PFC CCM operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum FREE peak of 260 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Peak repetitive reverse voltage	V _{RRM}		600	V						
Average rectified forward current	I _{F(AV)}	T _C = 117 °C	15							
Non-repetitive peak surge current	I _{FSM}	$T_J = 25 \ ^{\circ}C$	120	А						
Peak repetitive forward current	I _{FM}	$T_{C} = 117 \text{ °C}, f = 20 \text{ kHz}, d = 50 \%$	30							
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-				
Forward voltage		I _F = 15 A - 2.3				v			
	V _F	I _F = 15 A, T _J = 125 °C	-	1.6	1.9				
		I _F = 15 A, T _J = 150 °C	-	1.5	1.8				
		$V_{R} = V_{R}$ rated	-	-	50				
Reverse leakage current	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	200	μA			
		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	300				
Junction capacitance	CT	V _R = 600 V	-	11	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH			

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DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1 \text{ A}, dI_F/dt = 10$	00 A/µs, V _R = 30 V	-	18	22				
		$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50$	$I_F = 1 \text{ A}, \text{ d}I_F/\text{d}t = 50 \text{ A}/\mu\text{s}, \text{ V}_R = 30 \text{ V}$			-				
	t _{rr}	$I_{\rm F} = 15 \text{ A}, dI_{\rm F}/dt = 7$	-	17	32	ns				
		T _J = 25 °C		-	22	-	A			
		T _J = 125 °C		-	38	-				
Dook rooovon (ourront	I _{RRM}	T _J = 25 °C	l _F = 15 A dl _F /dt = 200 A/µs	-	3.1	-				
Peak recovery current		T _J = 125 °C	$V_{\rm R} = 390 \text{ V}$	-	4.6	-	A			
Deverse verse vers	0	T _J = 25 °C		-	37	-	nC			
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	92	-	10			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C			
Thermal resistance, junction to case per leg	R _{thJC}		-	1.4	1.8	°C/W			
Thermal resistance, junction to ambient per leg	R _{thJA}		-	-	70	0/10			
Approvimate weight				0.3		g			
Approximate weight				0.01					
Marking device		Case style TO-252AA (D-PAK)		15EWX06FN					

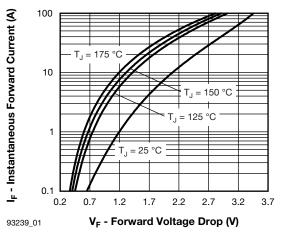
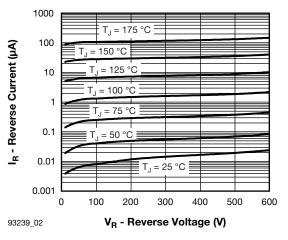


Fig. 1 - Typical Forward Voltage Drop Characteristics





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VS-15EWX06FN-M3

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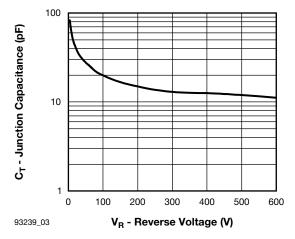


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

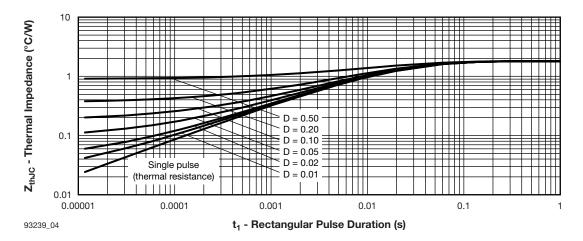
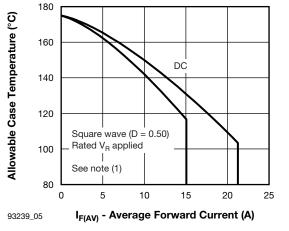
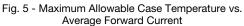


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics





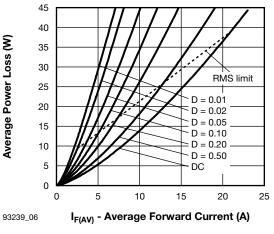


Fig. 6 - Forward Power Loss Characteristics

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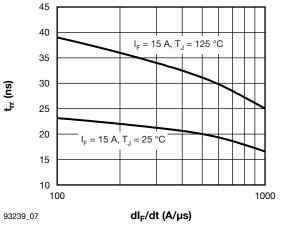


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt



- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$; Pd = forward power loss = $I_{F(AV)} \times V_{FM}$ at $(I_{F(AV)}/D)$ (see fig. 6); Pd_{REV} = inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at V_{R1} = rated V_R

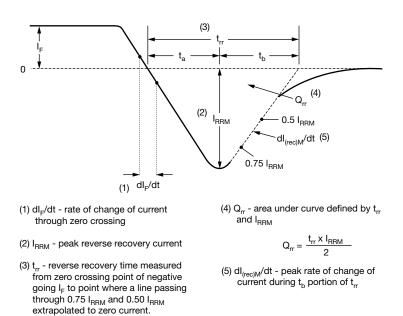
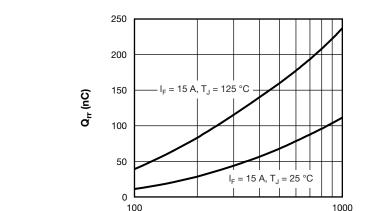


Fig. 9 - Reverse Recovery Waveform and Definitions



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dl_F/dt (A/µs) Fig. 8 - Typical Stored Charge vs. dl_F/dt

VS-15EWX06FN-M3

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ORDERING INFORMATION TABLE

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Device code	vs-	15	Е	w	x	06	FN	TRL	-M3
		2	3	4	5	6	7	8	9
	1	- Visl	hay Sen	nicondu	ctors pro	oduct			
	2	- Cur	rent rati	ng (15 =	= 15 A)				
	3	- Circ	cuit conf	iguratio	ו:				
		E =	Single	diode					
	4	- Pac	kage id	entifier:					
		W =	D-PAK	C					
	5	- X =	hyperfa	ist recov	ery time	e			
	6	- Vol	tage rati	ng (06 =	= 600 V)				
	7	- FN	= TO-25	52AA					
	8	• N	one = tu	ıbe					
		• TI	R = tape	e and ree	əl				
		• TI	RL = tap	e and r	eel (left	oriented	d)		
		• TI	RR = tap	be and r	eel (righ	nt orient	ed)		
	9	- Env	vironmer	ntal digit	:				
		-M3	3 = halog	gen-free	, RoHS	-complia	ant, and	termina	ations le

ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-15EWX06FN-M3	75	3000	Antistatic plastic tube							
VS-15EWX06FNTR-M3	2000	2000	13" diameter reel							
VS-15EWX06FNTRL-M3	3000	3000	13" diameter reel							
VS-15EWX06FNTRR-M3	3000	3000	13" diameter reel							

LINKS TO RELATED DOCUMENTS								
Dimensions	www.vishay.com/doc?95627							
Part marking information	www.vishay.com/doc?95176							
Packaging information	www.vishay.com/doc?95033							
SPICE model	www.vishay.com/doc?96041							





D-PAK (TO-252AA) "M"

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	NOTES		MILLIN	IETERS	INC	HES	NOTES
STNIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090	BSC	
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	REF.	
b3	4.95	5.46	0.195	0.215	3		L2	0.51 BSC		0.020 BSC		
с	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.040	
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
E	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

(4) Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁶⁾ Dimension b1 and c1 applied to base metal only

⁽⁷⁾ Datum A and B to be determined at datum plane H

⁽⁸⁾ Outline conforms to JEDEC[®] outline TO-252AA



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